Method For Forming Quantum Antidots In Semiconductors

Abstract

Disclosed herein is a method for forming quantum antidots in a gallium-arsenide / germanium semiconductor, said method comprising depositing carbon atoms in a first number of sweeps over one surface of a germanium substrate, diffusing carbon and germanium atoms in a second number of sweeps over the one surface of the germanium substrate, wherein the second number of sweeps is more than the first number of sweeps and nucleating an epitaxy gallium-arsenide film on the one surface of the substrate.

(No Suitable Figure)